New Product



VS-8EWL06FN-M3

Vishay Semiconductors

Ultralow V_F Ultrafast Rectifier, 8 A FRED Pt[®]



D-PAK (TO-252AA)

01	•	30
N/C		Anode

PRODUCT SUMMARY							
Package	D-PAK (TO-252AA)						
I _{F(AV)}	8 A						
V _R	600 V						
V _F at I _F	1.05 V						
t _{rr} (typ.)	60 ns						
T _J max.	175 °C						
Diode variation	Single die						

FEATURES

- Ultrafast recovery time, extremely low V_F and soft recovery
- 175 °C maximum operating junction temperature
- For PFC DCM operation
- Low leakage current
- Compliant to RoHS Directive 2002/95/EC
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Halogen-free according to IEC 61249-2-21 definition

DESCRIPTION

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS inverters or as freewheeling diodes. Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

APPLICATIONS

AC/DC SMPS 70 W to 400 W

e.g. laptop and printer AC adaptors, desktop PC, TV and monitor, games units and DVD AC/DC power supplies.

ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Peak repetitive reverse voltage	V _{RRM}		600	V				
Average rectified forward current	I _{F(AV)}	T _C = 158 °C	8					
Non-repetitive peak surge current I _{FSM}		T _J = 25 °C	140	А				
Peak repetitive forward current	I _{FM}	T_{C} = 158 °C, f = 20 kHz, d = 50 %	16					
Operating junction and storage temperatures	T _J , T _{Stg}		- 65 to 175	°C				

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS MIN. TYP. MAX				UNITS		
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA		-	-			
Forward voltage	VF	I _F = 8 A	-	0.96	1.05	V		
		I _F = 8 A, T _J = 150 °C	-	0.81	0.86]		
Poverse leekage ourrest		$V_{R} = V_{R}$ rated	-	-	5			
Reverse leakage current I _R		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$ -		-	100	μA		
Junction capacitance	CT	V _R = 600 V	-	8	-	pF		
Series inductance	L _S	Measured lead to lead 5 mm from package body - 8 -		-	nH			

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RoHS COMPLIANT HALOGEN FREE

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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 $^{\circ}$ C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
			$I_F = 1 \text{ A}, dI_F/dt = 50 \text{ A}/\mu \text{s}, V_R = 30 \text{ V}$		87	-		
Reverse recovery time	+	$I_F = 1 \text{ A}, dI_F/dt = 10$	-	60	100	ns		
neverse recovery time	t _{rr}	T _J = 25 °C		-	170	-	115	
		T _J = 125 °C	I _F = 8 A dI _F /dt = 200 A/μs V _R = 390 V	-	250	-		
Dook rooovony ourront	1	T _J = 25 °C		-	15	-	А	
Peak recovery current	I _{RRM}	T _J = 125 °C		-	20	-	~	
	0	T _J = 25 °C		-	1.3	-	uC	
Reverse recovery charge Q _{rr}		T _J = 125 °C		-	2.6	-	uC	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		- 65	-	175	°C	
Thermal resistance, junction to case per leg	R _{thJC}		-	1.8	2.2	°C/W	
Approximate weight				0.3		g	
Approximate weight			0.01			oz.	
Marking device		Case style D-PAK (TO-252AA)		8EWL	.06FN		





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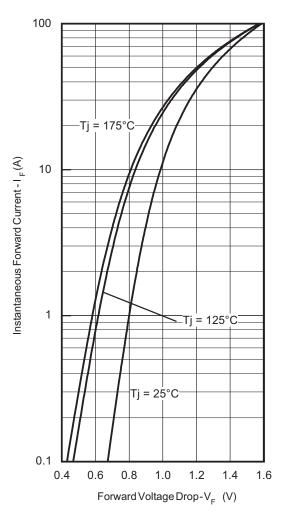


Fig. 1 - Typical Forward Voltage Drop Characteristics

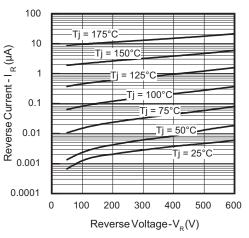


Fig. 2 - Typical Values of Reverse Current vs. **Reverse Voltage**

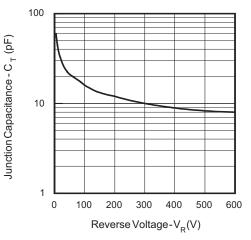


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

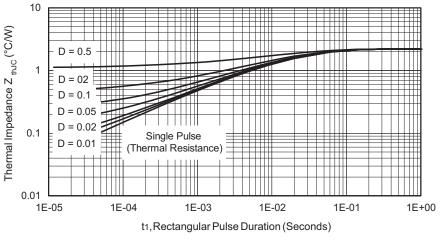


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics

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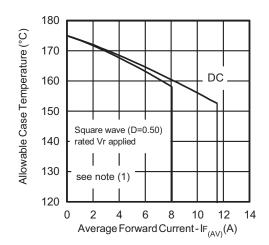


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

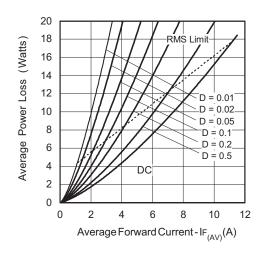


Fig. 6 - Forward Power Loss Characteristics

Note

- ⁽¹⁾ Formula used: $T_C = T_J (Pd + Pd_{REV}) \times R_{thJC}$; $\begin{array}{l} \mathsf{Pd} = \mathsf{Forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \, x \, \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{Inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \, x \, \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{Rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

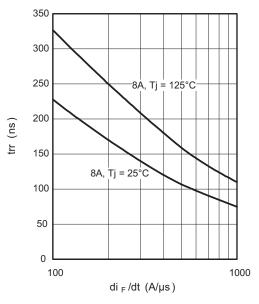


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

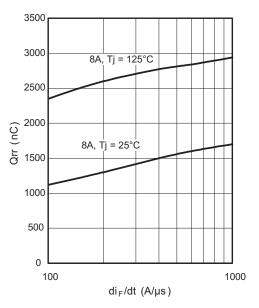


Fig. 8 - Typical Stored Charge vs. dl_F/dt

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5

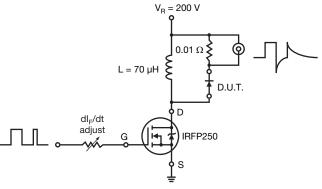


Fig. 9 - Reverse Recovery Parameter Test Circuit

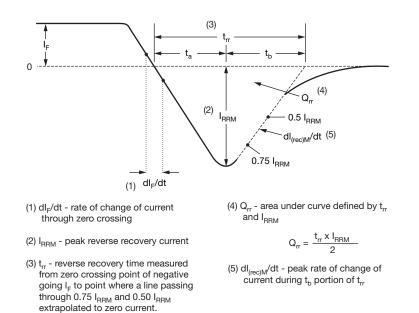


Fig. 10 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

Device code	VS-	8	E	w	L	06	FN	TRL	-M3
		2	3	4	5	6	7	8	9
	1	- Vis	hay Sen	nicondu	ctors pro	oduct			
	2	- Cui	rent rati	ng (8 =	8 A)				
	3	- Cire	cuit conf	iguratio	n:				
		E =	Single	diode					
	4	- Pao	ckage id	entifier:					
		W :	= D-PAK	(
	5	- L=	$Low\;V_F$, fast reo	covery				
	6	- Vol	tage rati	ng (06 =	= 600 V))			
	7	- FN	= TO-25	52AA					
	8	- • N	one = T	ube					
		• T	R = Tap	e and re	el				
		• T	RL = Ta	pe and	reel (left	oriente	ed)		
		• T	RR = Ta	pe and	reel (rig	ht orien	ted)		
	9	- Env	/ironmer	ntal digit					
		-M3	3 = Halo	gen-free	e, RoHS	compli	ant and	termina	tions le

ORDERING INFORMATION (Example) **QUANTITY PER T/R** PREFERRED P/N MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION VS-8EWL06FN-M3 75 3000 Antistatic plastic tube VS-8EWL06FNTR-M3 2000 2000 13" diameter reel 3000 3000 VS-8EWL06FNTRL-M3 13" diameter reel VS-8EWL06FNTRR-M3 3000 3000 13" diameter reel

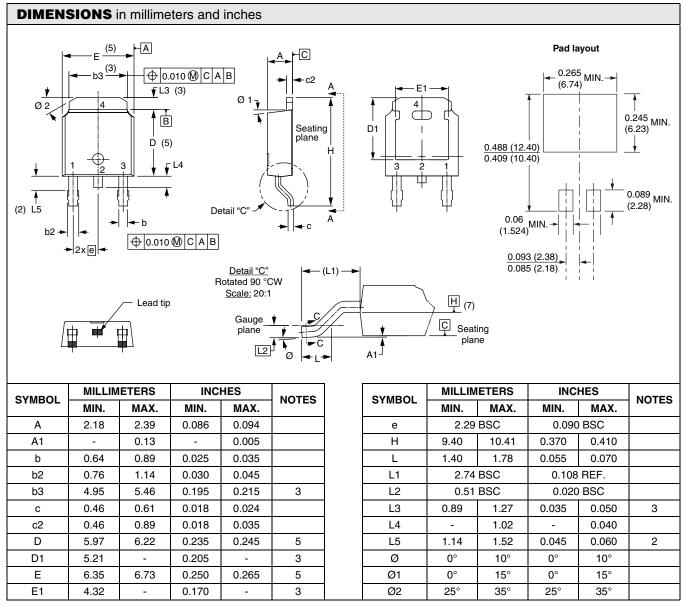
LINKS TO RELATED DOCUMENTS						
Dimensions <u>www.vishay.com/doc?95016</u>						
Part marking information	www.vishay.com/doc?95176					
Packaging information	www.vishay.com/doc?95033					
SPICE model	www.vishay.com/doc?95373					

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Vishay High Power Products

D-PAK (TO-252AA)



Notes

- $^{(1)}\,$ Dimensioning and tolerancing as per ASME Y14.5M-1994
- ⁽²⁾ Lead dimension uncontrolled in L5
- ⁽³⁾ Dimension D1, E1, L3 and b3 establish a minimum mounting surface for thermal pad
- (4) Section C C dimension apply to the flat section of the lead between 0.13 and 0.25 mm (0.005 and 0.10") from the lead tip
- ⁽⁵⁾ Dimension D, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- ⁽⁶⁾ Dimension b1 and c1 applied to base metal only
- ⁽⁷⁾ Datum A and B to be determined at datum plane H
- ⁽⁸⁾ Outline conforms to JEDEC outline TO-252AA



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